

Future cell technology

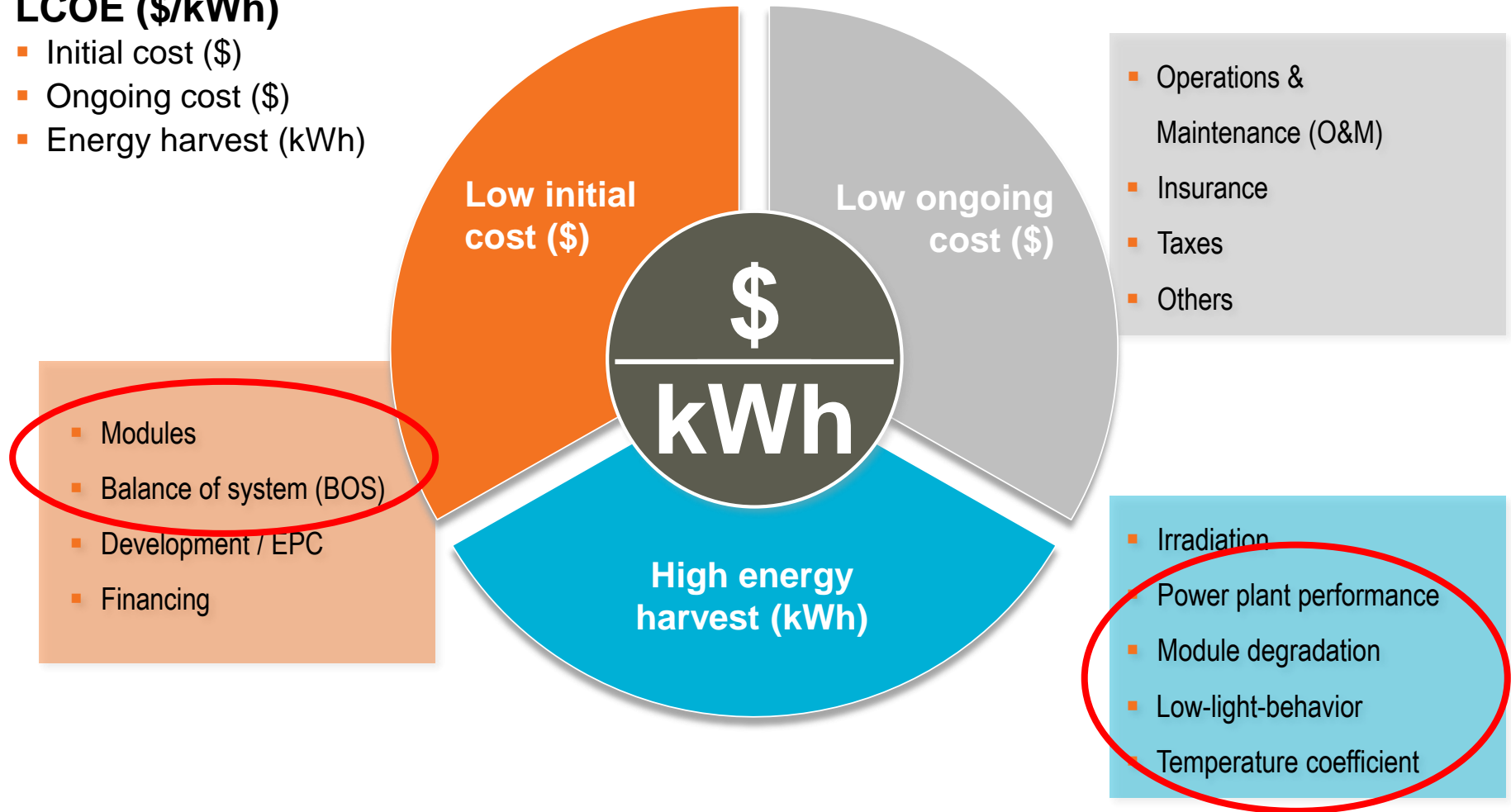
Future PV forum 2017, Munich, June 1st, 2017

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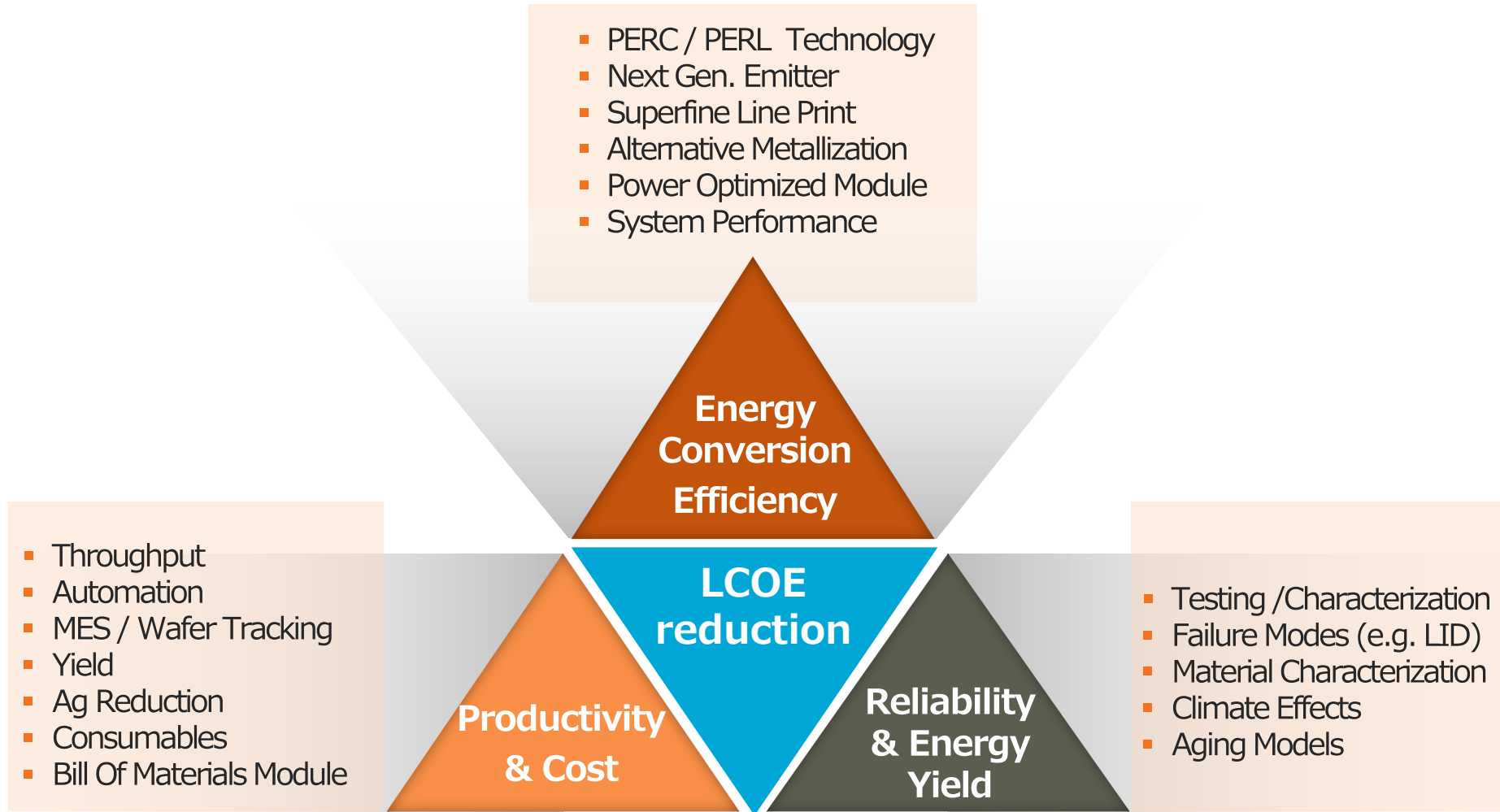
LCOE (\$/kWh)

- Initial cost (\$)
- Ongoing cost (\$)
- Energy harvest (kWh)



Electricity is commodity: main parameter is LCOE

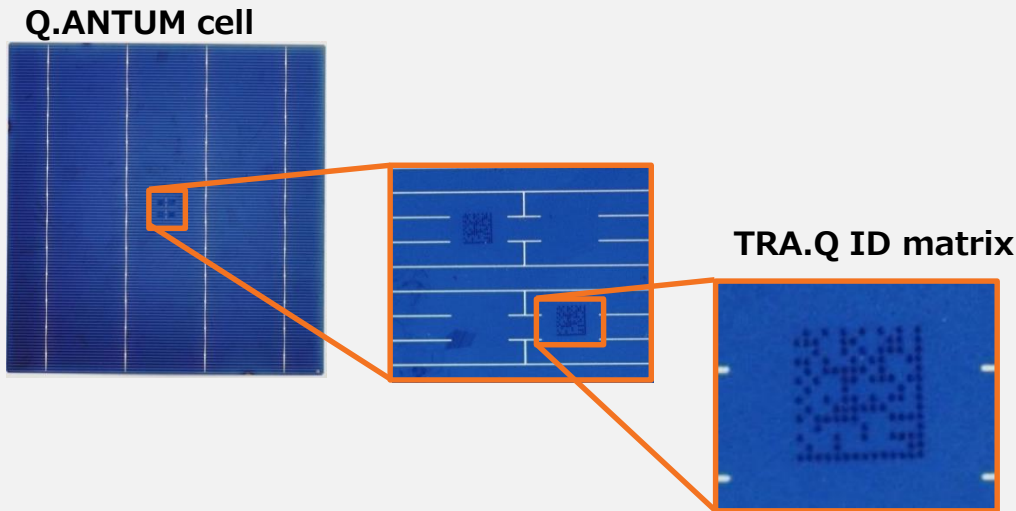
New technologies: optimization of productivity, efficiency and reliability



- **10 GW/a cell production**
 - ~1 800 000 000 cells per year
 - ~ 5 000 000 cells per day
 - ~ 60 cells per second
 - ~ 800 process tools

- **Needs fully automated production and manufacturing control**

Single wafer tracking for efficient development and manufacturing control



- Each wafer marked with unique ID matrix
- ID can be linked with relevant process and measurement stations
- Worldwide standardization within SEMI
- TRA.Q manufacturing experience at Hanwha Q Cells since 2009

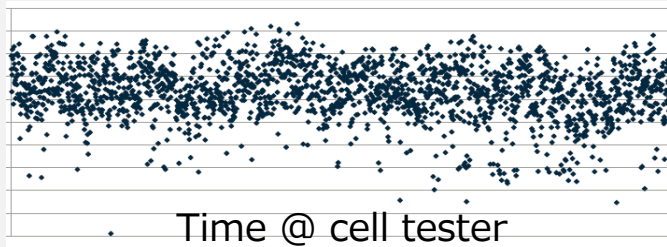
→ **Via TRA.Q:** Correlation of process parameters with Inline measured data and cell parameters possible

- Very powerful for GW scale production → efficient data mining possible
- Without any additional cell handling and cell withdrawals

S. Wanka et al. "Tra.Q: Laser Marking for Single Wafer Identification- Production Experience of 100 Million Wafers" in Proc. 26th EUPVSEC, 821-826, Hamburg, Germany, 2011

Continuous improvement Analysis of wafer material influence

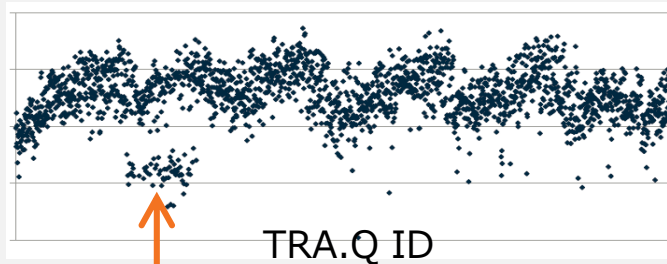
Cell efficiency (arb. Units)



Efficiency Data from 2300 cells ordered by time

→ Broad distribution of cell efficiency

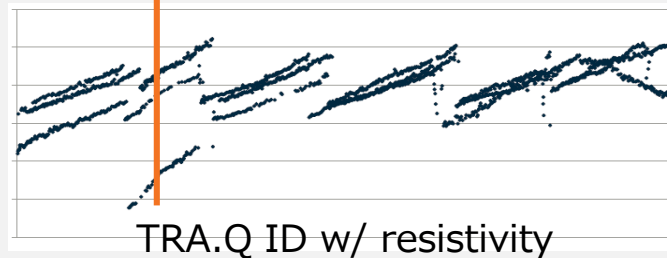
Cell efficiency (arb. Units)



Efficiency Data ordered by TRA.Q ID

→ Distribution of cell efficiency shows pattern

Cell efficiency (arb. Units)



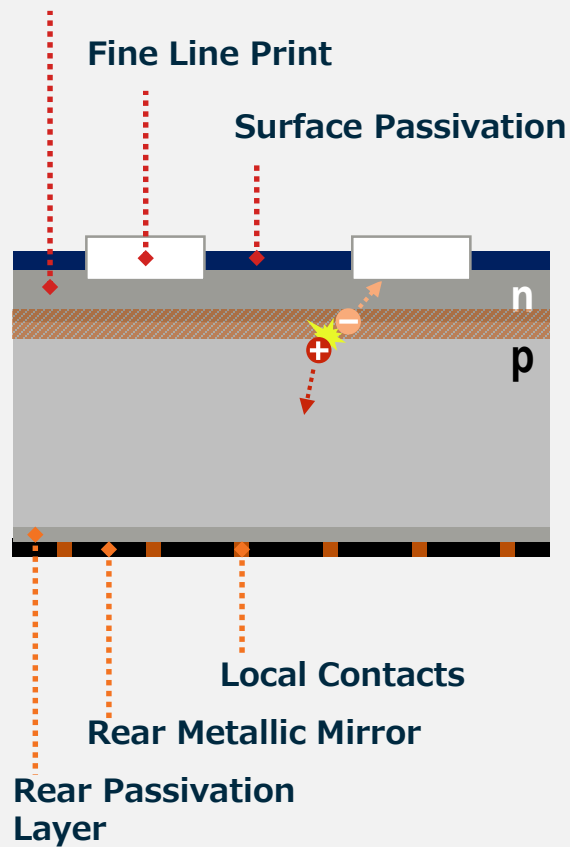
Wafer base resistivity ordered by TRA.Q ID

→ Distribution shows characteristic pattern

Increase efficiency cost effectively

Evolutionary Cell Device Optimization:

Emitter Doping Profile



Front

Rear

Targets

- Reduced light shading and silver consumption
- Increased blue response

Approach

- Fine line contacts
→ reduced metal coverage, contact to optimized emitter
- Emitter doping profile
→ reduced Auger recombination
- Surface passivation
→ optimized emitter passivation

Targets

- Improve surface passivation, increased red response

Approach

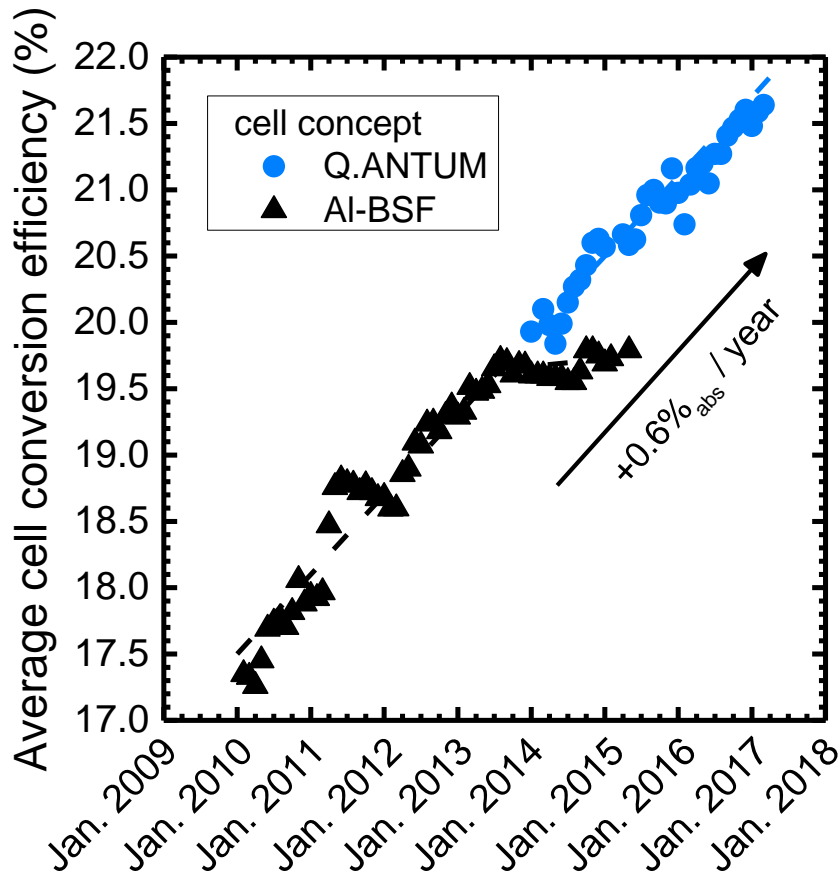
- Optimized rear passivation layer
→ reduced recombination
- Improved rear metallic mirror
→ increased light trapping
- Passivated local contacts
→ reduced recombination

Boundary condition

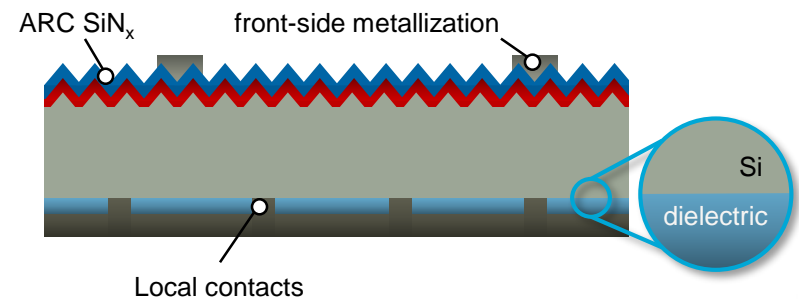
- Cost effective and module compatibility

Increase efficiency cost effectively

Evolutionary Cell Device Optimization:



Q.ANTUM Technology^[2,3]

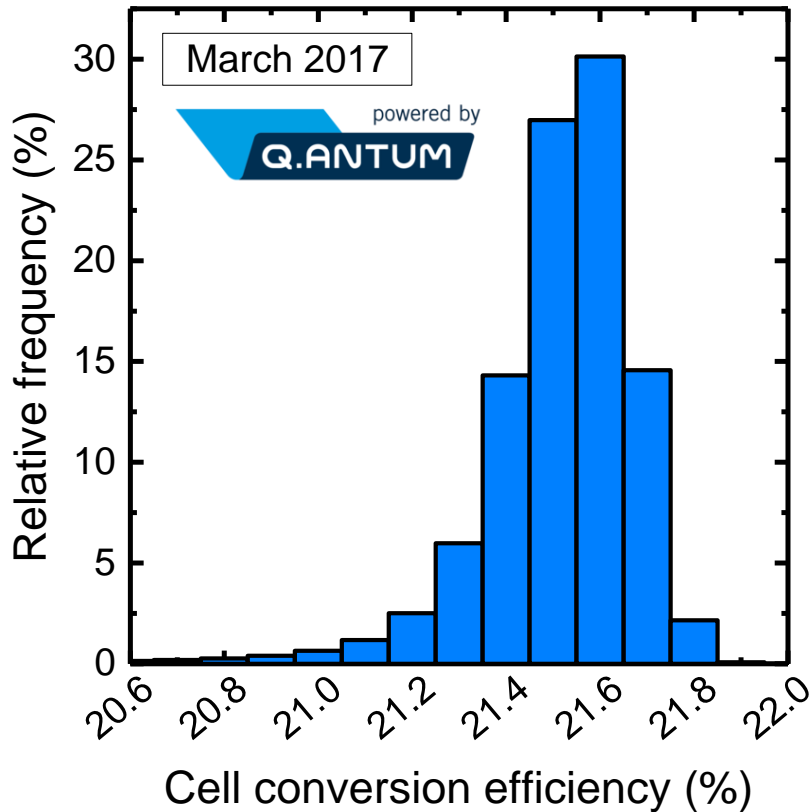


- Increased photo generation
- Reduced rear-surface recombination
- Additional features to PERC

Q CELLS
YIELD SECURITY

- ✓ ANTI PID TECHNOLOGY (APT)
- ✓ HOT-SPOT PROTECT (HSP)
- ✓ TRACEABLE QUALITY (TRA.Q™)
- ✓ ANTI LID TECHNOLOGY (ALIDT)

[1] J. Mandelkorn and J.H. Lamneck "Simplified Fabrication of Back Surface Electric Field Silicon Cells and ..." in Proc. 9th IEEE PVSC, 66-71, Silver Springs, USA, 1972.
 [2] P. Engelhart *et al.* "Q.ANTUM - Q-Cells Next Generation High-Power Silicon Cell & Module Concept" in Proc. 26th EUPVSEC, 821-826, Hamburg, Germany, 2011.
 [3] A. Mohr *et al.* "20%-Efficient Rear Side Passivated Solar Cells in Pilot Series ..." in Proc. 26th EUPVSEC, 2150-2153, Hamburg, Germany, 2011

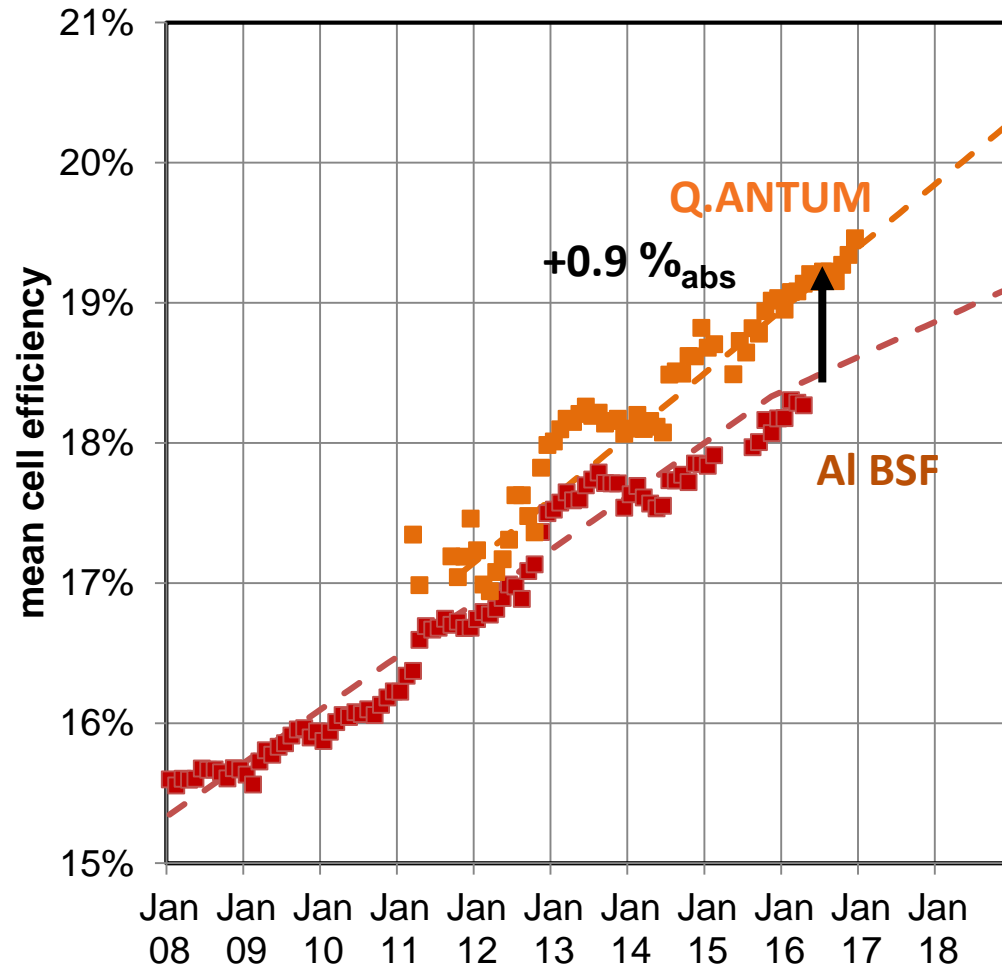


Conversion efficiency distribution

- Very tight distribution with efficiencies > 21.5 %
- Further improvement potential by optics and reduced recombination losses
- Efficiency headroom of Q.ANTUM exceeds 24 %

Increase efficiency cost effectively

Multi solar cell efficiency development



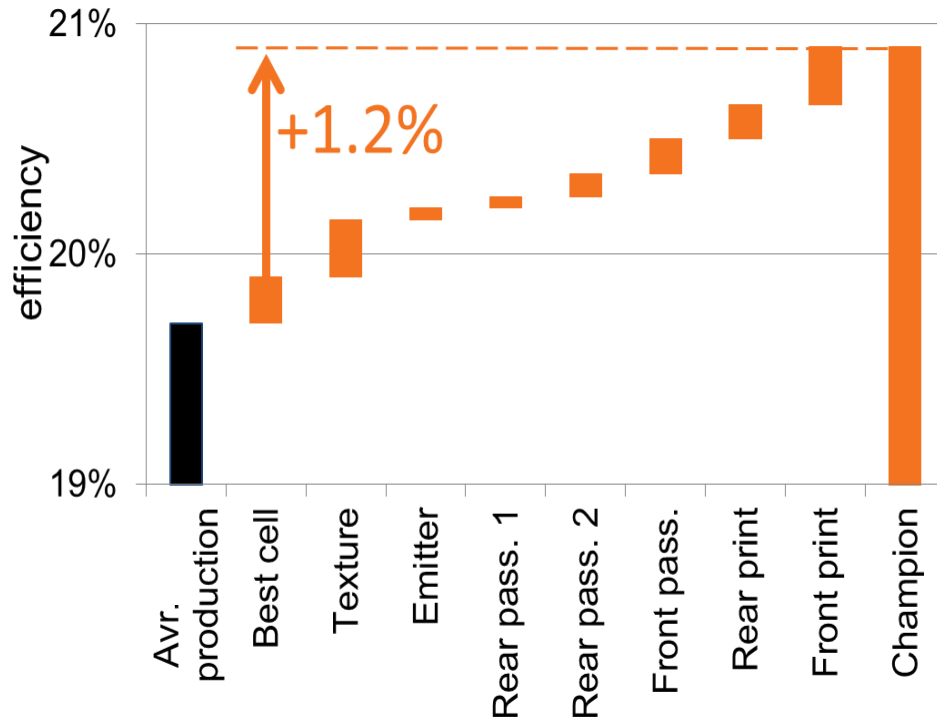
- Similar results using multi crystalline wafer
- > 5 years of high-quality **Q.ANTUM mass production:**
 - median cell efficiency: > 19.8 %
 - N_{cell} increase: + 0.5 %_{abs}/a
 - Silver consumption: - 50 %
 - Upgrade of existing tool set
 - Throughput increase
- Currently ~ 3 GW Q.ANTUM multi capacity

B. Klöter et. al., 32nd EU-PVSEC 2016

Increase efficiency cost effectively

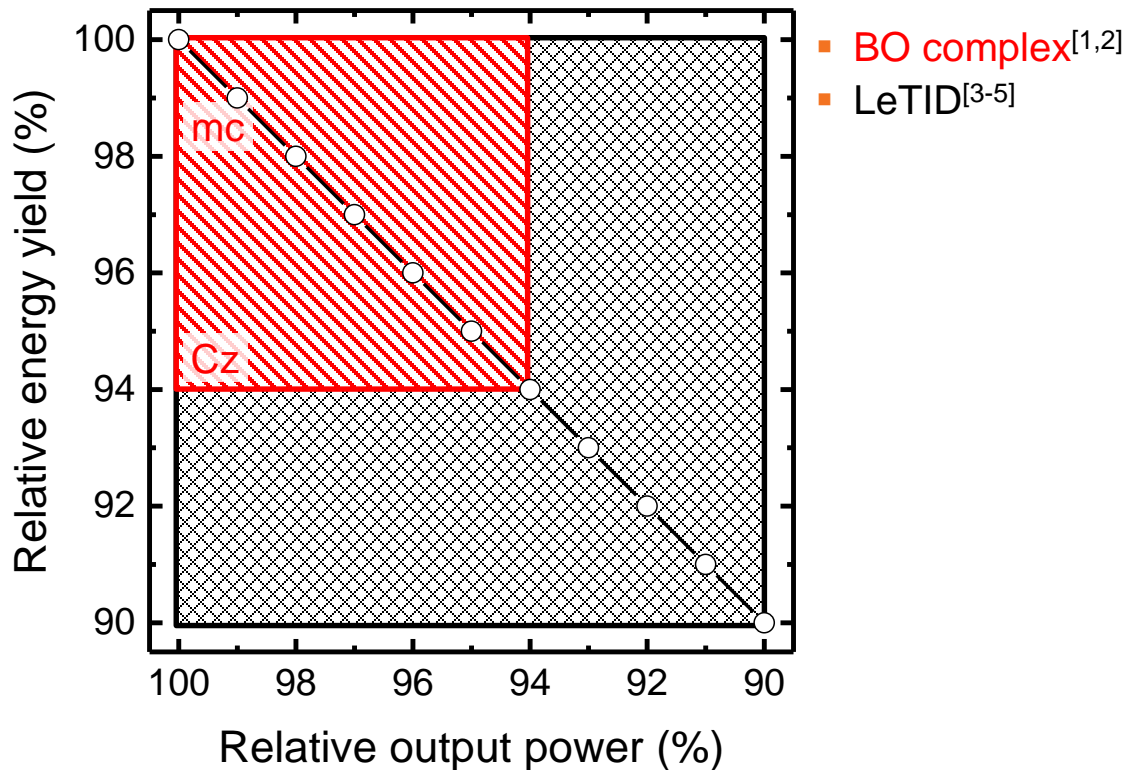
Q.ANTUM Multi: Champion cell result

measures of champion cell improvement



- 5 years of high-quality Q.ANTUM production:
 - Median cell efficiencies of 19.8 %
- Further improved optics and reduced recombination losses
- Champion cell efficiency 21.9%*
- Cost effective processes suitable for mass production
- Efficiency headroom of Q.ANTUM multi exceeds 22 %

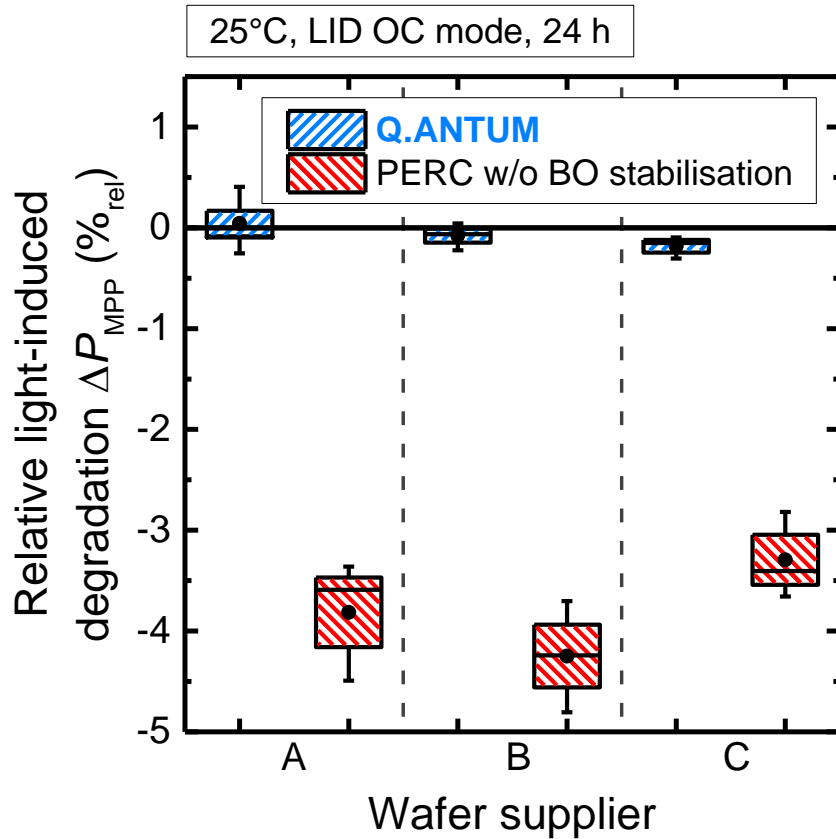
LID degradation



LID degradation

- More severe w/ increasing eta
- If not suppressed, severe problem for Cz and mc-Si PERC cells
- Dedicated measures mandatory** to suppress degradation

[1] S. Rein *et al.*, in: Proc. 17th EUPVSEC, 1555–1560, Munich, Germany, 2001.
[2] J. Schmidt and K. Bothe, Phys. Rev. B **69**, 024107, 2004.
[3] K. Ramspeck *et al.* in Proc. 27th EUPVSEC, 861–865, Frankfurt, Germany, 2012.
[4] F. Fertig *et al.*, phys. stat. sol. (RRL) **9**, 41–46, 2015.
[5] F. Kersten *et al.*, Sol. Energ. Mat. Sol Cells **142**, 83–86, 2015.



LID due to BO complex

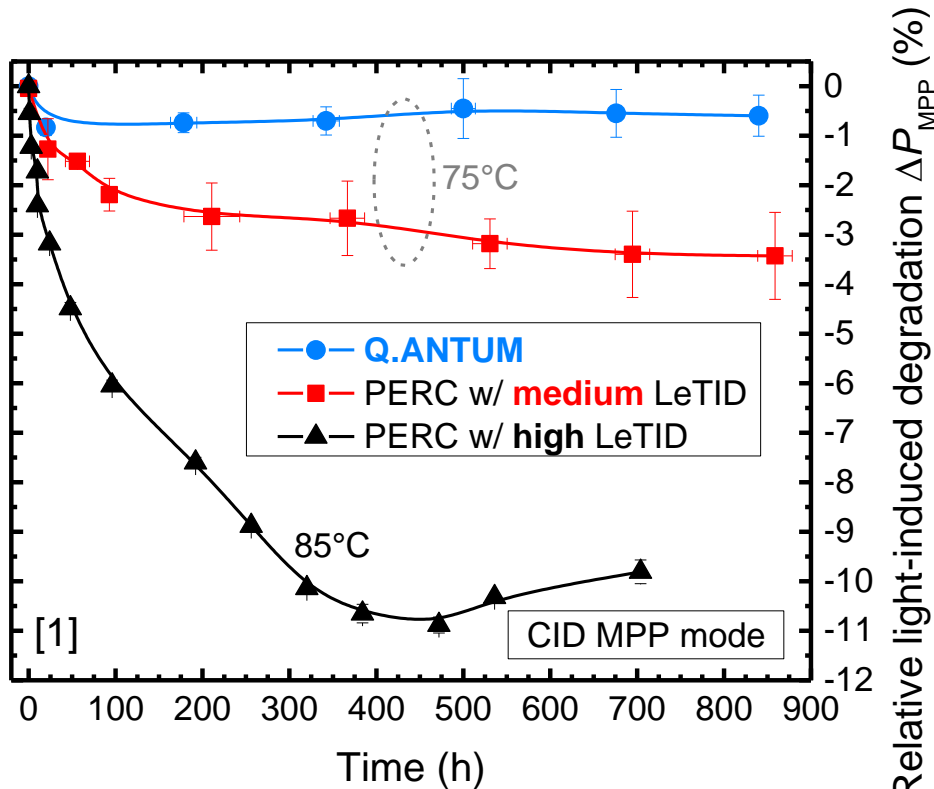
- First observed in the 70s^[1]
 - Most prominent LID mechanism in commercial Cz silicon
 - More severe w/ increasing eta
 - Possibility to permanently deactivate has been first presented in 2006^[2]
 - Intensively researched by many groups
 - Solutions for MP commercially available
- Q.ANTUM suppresses LID due to BO complex

[1] H. Fischer and W. Pschunder "Investigation of Photon and Thermal Induced Changes in Silicon Solar Cells" in Proc. 10th IEEE PVSC, 404-411, Palo Alto, USA, 1973.

[2] A. Herguth *et al.* "A New Approach to Prevent the Negative Impact of the Metastable Defect in Boron Doped Cz ..." in Proc. 4th WCPEC, 940-943, Hawaii, USA, 2006

LeTID: Light and elevated Temperature Induced Degradation

mc silicon

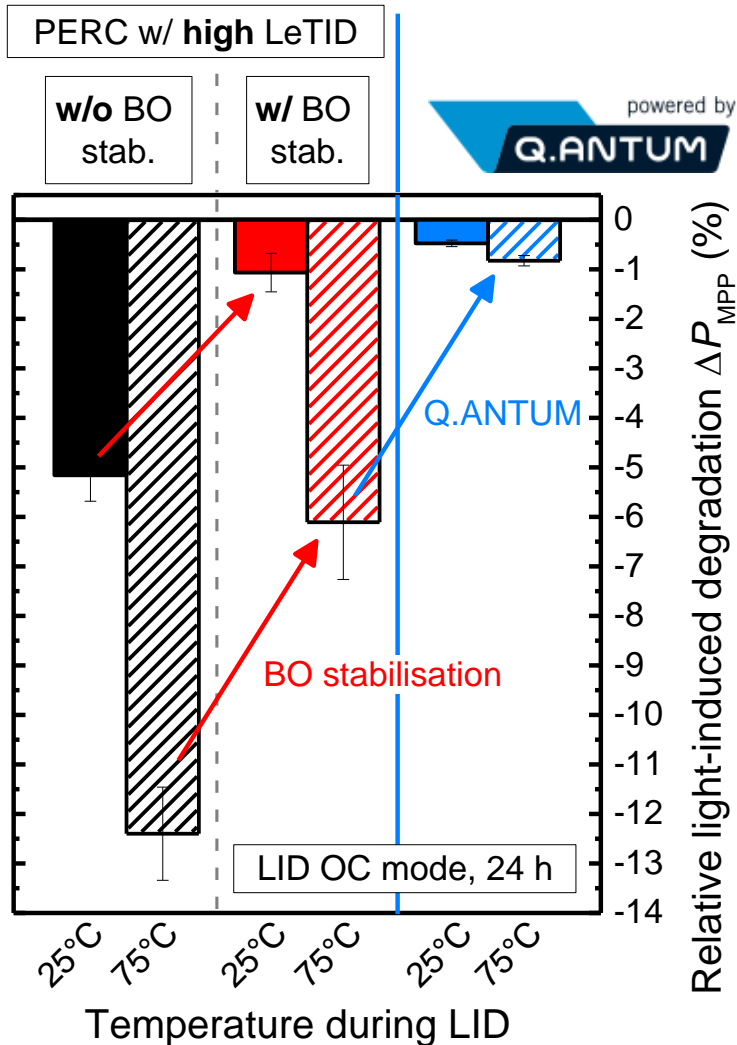


Characteristics and implications

- First observed in mc-Si PERC
- If not suppressed, severe problem for mc-Si PERC cells
- Forms under charge carrier injection at elevated temperatures
- Formation kinetics depend on temperature and excess charge carrier density
- $T \uparrow, \Delta n \uparrow \rightarrow$ formation rate \uparrow
- Severity can be manipulated
- Q.ANTUM suppresses LeTID in mc-Si

[1] F. Kersten *et al.* "Degradation of multicrystalline silicon solar cells and modules after illumination at elevated temperature," Sol. Energ. Mat. Sol Cells **142**, 83–86, 2015.

Increase reliability LeTID in PERC Solar Cells and Module



Cz silicon

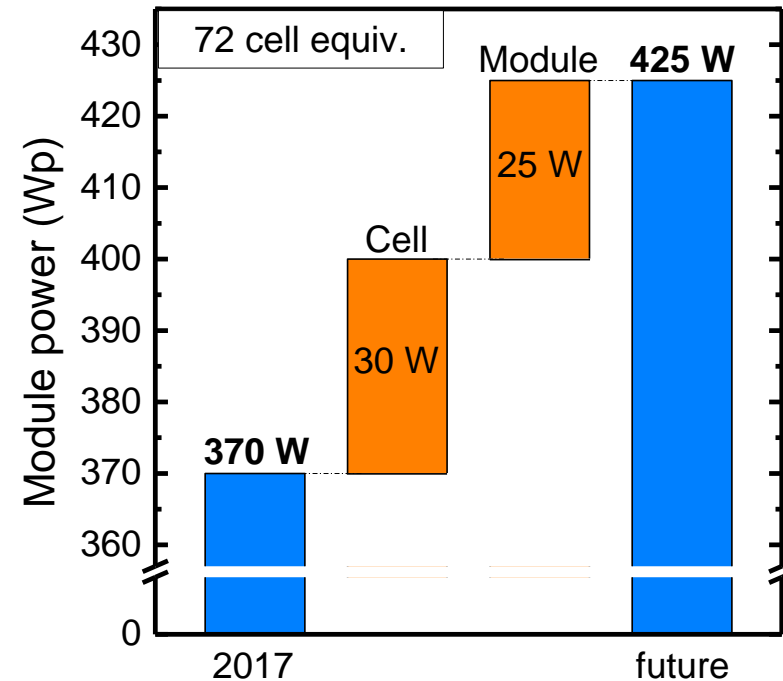
- **LeTID** not only in *p*-type mc PERC but also in *p*-type Cz PERC
 - big challenge for MP of *p*-type Cz-Si PERC cells
 - much more difficult to control than BO complex formation
- **Q.ANTUM** technology suppresses LID and LeTID in Cz silicon

- Electricity is commodity, **LCOE** is main development criteria, price reduction will continue
→ **cost per piece**, **efficiency** and **reliability** are crucial

- Increase **productivity** in multi GW production:
 - Several Mio cells per day needs powerful MES
 - **Single wafer tracking** for efficient HVM

- Increase **efficiency** cost effectively:
 - Still **significant headroom** for efficiency improvements via evolutionary development
 - keep **Q.ANTUM platform** for the coming years

- Increase **reliability**:
 - Degradation (e.g. LID/LeTID) can severely affect energy yield
 - Dedicated measures to suppress any degradation



Thank you.

